FAIRCHILD SEMICONDUCTOR®

March 2007

PDP SPM™

FVP18030IM3LSG1 Sustain

Features

- Use of high speed 300V IGBTs with parallel FRDs
- Single-grounded power supply by means of built-in HVIC
- Sufficient current driving capability for IGBTs due to adding a buffer
- Isolation rating of 1500Vrms/min.
- Low leakge current due to using an insulated metal substrates

Applications

- Sustain Part of a PDP(Plasma display panel)

General Description

It is an advanced samart power module(SPM™) that Fairchild has newly developed and designed to provide very compact and optimized performance for the sustaining circuit of PDP driving system. It contains HVICs, buffers and low-loss high speed IGBTs that are needed to compose the sustaining circuits. Under voltage lock-out protection function enhances the system reliabilty. The high speed built-in HVIC provides opto-coupler-less single power supply IGBT gate driving capability that further reduce the overall system size of PDP and the buffer provides high current driving capability of IGBTs.

Package Outlines

Figure 1.

Pin Configurations

Top View

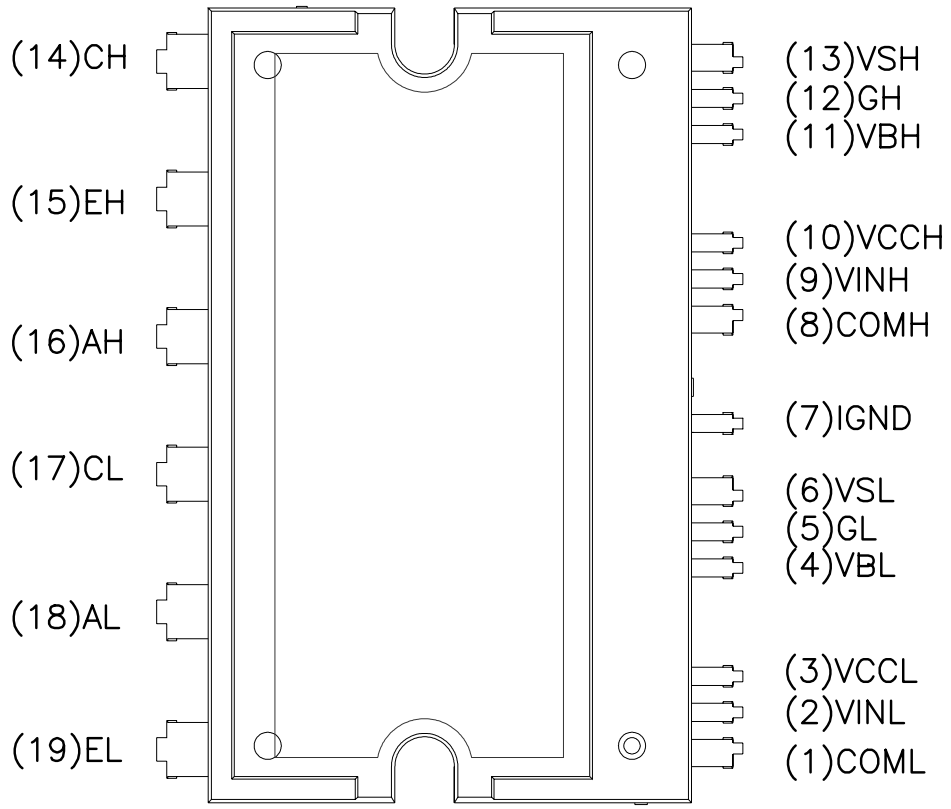


Figure 2.

Pin Descriptions

Pin Number	Pin Name	Pin Descriptions
1	COML	Low-side Signal Ground
2	VINL	Low-side Signal Input
3	VCCL	Low-side Supply Voltage for HVIC
4	VBL	Low-side Floating Supply Voltage for Buffer IC and IGBT Driving
5	GL	Low-side Gate
6	VSL	Low-side Floating Ground for Buffer IC and IGBT Driving
7	IGND	IMS Ground
8	COMH	High-side Signal Ground
9	VINH	High-side Signal Input
10	VCCH	High-side Supply Voltage for HVICg
11	VBH	High-side Floating Supply Voltage for Buffer IC and IGBT Driving
12	GH	High-side Gate
13	VSH	High-side Floating Ground for Buffer IC and IGBT Driving
14	CH	High-side IGBT Collector
15	EH	High-side IGBT Emitter
16	AH	High-side Diode Anode
17	CL	Low-side IGBT Collector
18	AL	Low-side Diode Anode
19	EL	Low-side IGBT Emitter

Internal Equivalent Circuit and Input/Output Pins (Bottom View)

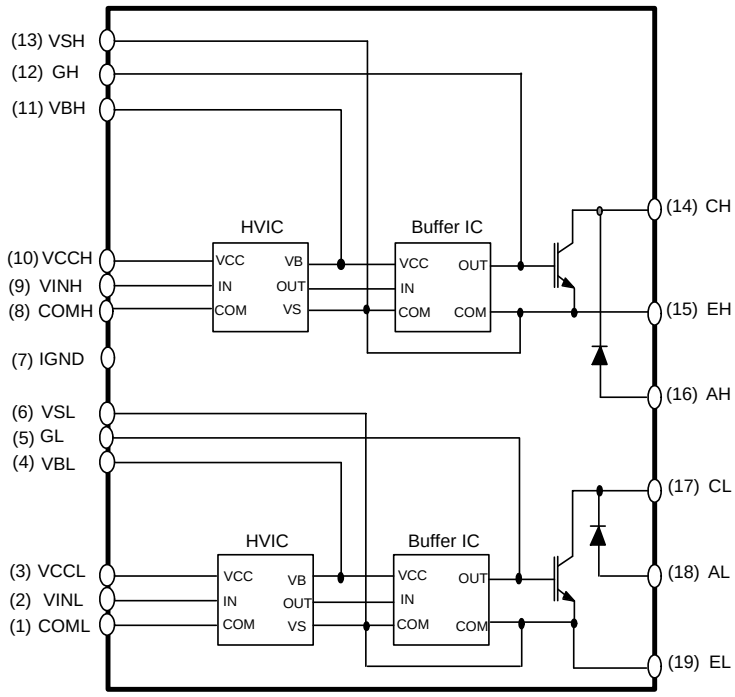


Figure 3.

Absolute Maximum Ratings (T_C = 25°C, Unless Otherwise Specified)

Symbol	Parameter	Conditions	Rating	Units
VCC	Control Supply Voltage	Applied between VCCL-COML, VCCH - COMH	20	V
VBS	Control Bias Voltage	Applied between VBL - VSL, VBH - VSH	20	V
VIN	Input Signal Voltage	Applied between VINL-COML,VINH - COMH	-0.3~17	V

Symbol	Parameter	Conditions	Rating	Units
VCE	Collector to Emitter Voltage	Between CL to EL, Between CH to EH $V_{GH-EH}=V_{GL-EL}=0V$, $I_{CH}=I_{CL}=250\mu A$	300	V
VRRM	Peak Repetitive Reverse Voltage	Between CH to AH, Between CL to AL $I_{AH}=I_{AL}=250\mu A$	300	V
VIN	Input Signal Voltage	VINL, VINH	-0.3 to Vcc+0.3	V
I_C	Collector Current Continuous	Between CL to EL, Between CH to EH	180	A
$I_{F(AV)}$	Average Rectified Forward Current	Between CH to AH, Between CL to AL	10	A
I_{CP}	Pulsed Collector Current	Between CL to EL, Between CH to EH (Note1)	450	A
I_{FP}	Pulsed Diode Current	Between CH to AH, Between CL to AL (Note1)	100	A

Notes :

1. Pulse Width = 100μsec, Duty = 0.1; half sine wave

   *I_{cp} limited by MAX T_j

Symbol	Parameter	Conditions	Rating	Units
Pd	IGBT Dissipation	Tc=25°C per IGBT	167	W
		Tc=100°C per IGBT	67	W
	FRD Dissipation	Tc=25°C per diode	34	W
		Tc=100°C per diode	14	W
Tj	Operating Junction Temperture		-20 ~ 150	°C
T_C	Module Case Operation Temperature		-20 ~ 125	°C
T_{STG}	Storage Temperature		-40 ~ 125	°C
V_{ISO}	Isolation Voltage	60Hz, Sinusoidal, AC 1 minute, Connection Pins to IMS substrate	1500	V_{rms}

Thermal Resistance

Symbol	Parameter	Conditions	Min.	Max.	Units
$R_{th(j-c)}$	Junction to Case Thermal Resistance	Between CH to EH, Between CL to EL per IGBT	-	0.75	°C/W
		Between CH to AH, Between CL to AL per Diode	-	3.70	°C/W

Electrical Characteristics (T_c = 25°C, Unless Otherwise Specified)

Symbol	Parameter	Conditions		Min.	Typ.	Max.	Units
I_{QCC}	Quiescent VCC Supply Current	VCC = 15V VINL, VINH = 0V	VCCL-COML, VCCH-COMH	-	-	100	μA
I_{QBS}	Quiescent VBS Supply Current	VBS = 15V VINL, VINH= 0V	VBL- VSL, VBH- VSH	-	-	500	μA
UV_{BSD}	Supply Circuit Under Voltage Protection	Detection Level		10.1	11.3	12.5	V
UV_{BSR}		Reset Level		10.5	11.7	12.9	V
$VIN_{(ON)}$	ON Threshold Voltage	Applied between VINL-COML, ,VINH - COMH		3.0		-	V
$VIN_{(OFF)}$	OFF Threshold Voltage			-	-	0.8	V

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
$V_{CE(SAT)}$	IGBT Collector-Emitter Saturation Voltage	VCC = VBS = 15V VIN = 5V	I_C = 40A, T_J = 25°C	-	-	1.4	V
			I_C = 180A, T_J = 25°C	-	1.9	-	V
V_F	Diode Forward Voltage	VIN = 0V	I_C =10A, T_J = 25°C	-	-	1.4	V
td_{ON}	Switching Times	VCE=200V, VCC= VBS=15V Ic = 20A VIN = 0V ↔ 5V , Inductive Load Tc = 25°C (Note2)		-	230	-	ns
t_r				-	54	-	ns
td_{OFF}				-	260	-	ns
t_F				-	108	-	ns
I_{CES}	Collector-Emitter Leakage Current	VCE = 300V		-	-	250	μA
I_R	Diode Anode-Cathode Leakage Current	Between EH to CH Between EL to CL	$V_{Anode-Cathode}$=300V			250	μA

Notes :

2. t_{ON} and t_{OFF} include the propagation delay time of internal drive IC. For the detailed information, please see Figure 4.

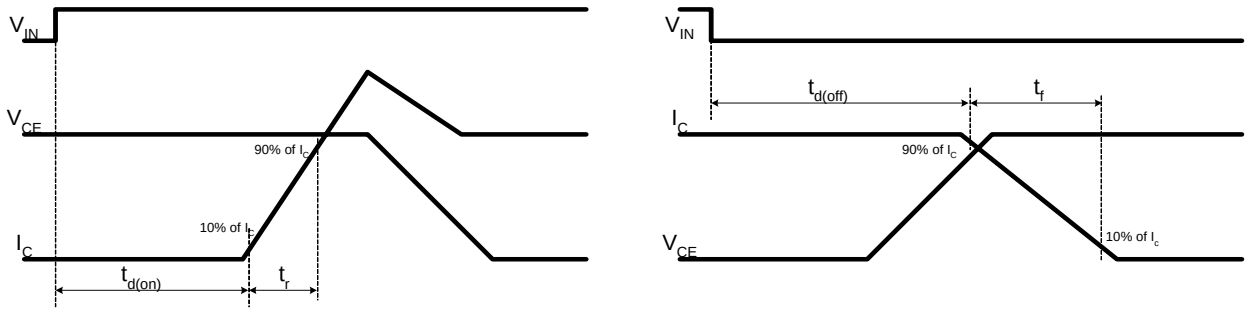


Figure 4. Switching Time Definition

Typical Performance Characteristics

Figure 5. Typical Output Characteristics

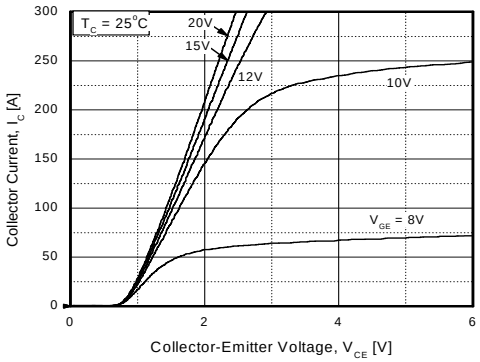


Figure 6. Typical Output Characteristics

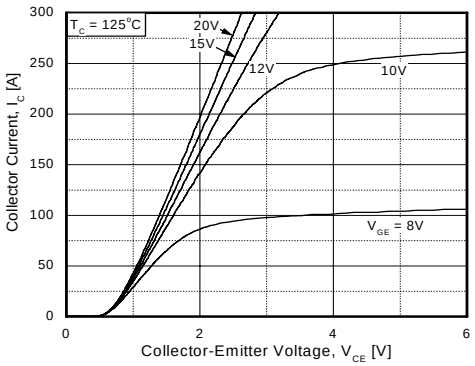


Figure 7. Typical Forward Voltage Drop

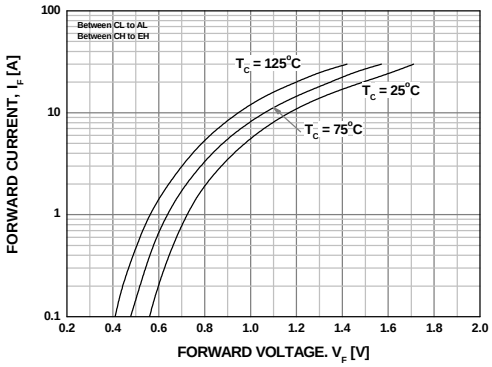
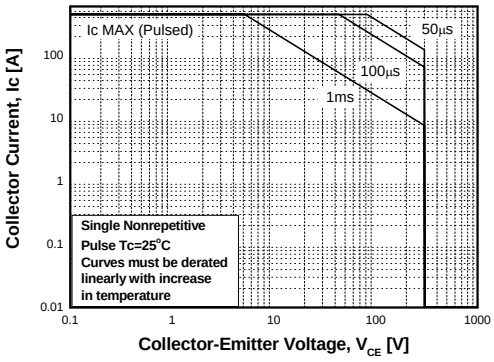


Figure 8. Typical Forward Voltage Drop



Mechanical Characteristics and Ratings

Parameter	Conditions		Limits			Units
			Min.	Typ.	Max.	
Mounting Torque	Mounting Screw: - M3	Recommended 0.62N•m	0.51	0.62	0.72	N•m
Device Flatness		Note Figure 5	0	-	+100	μm
Weight			-	13.4	-	g

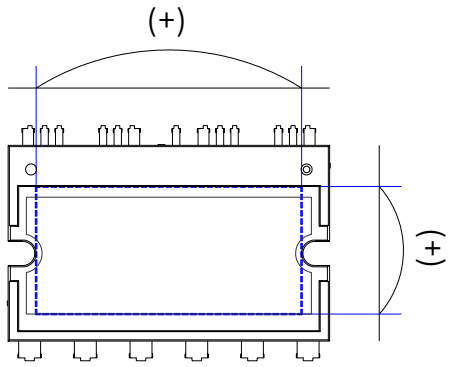


Figure 9. Flatness Measurement Position

Detailed Package Outline Drawings

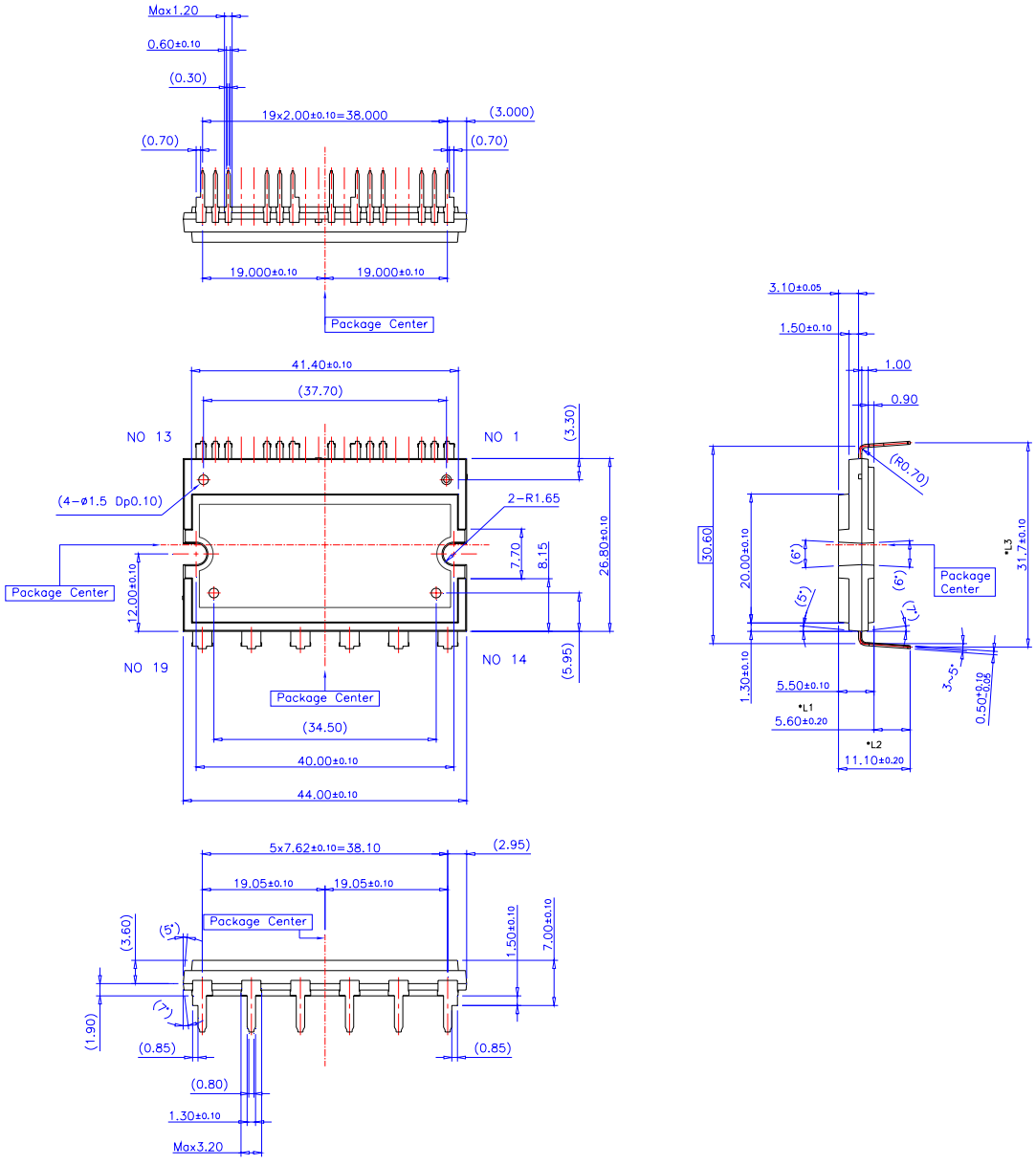


Figure 10.

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